PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031
U.S. Eight and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Substitute	e for form 1449A/PTO			Record	Complete if Known
INEO	DMATION	DISC	OSTIDE	Application Number	10/712,062
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Filing Date	November 14, 2003
SIA				First Named Inventor	Shunpei YAMAZAKI et al.
	(use as many sheets	as necessi	1ry)	Group Art Unit	2826
				Examiner Name	F. Abraham
Sheet	ı	of	1	Attorney Docket Number	0756-7218

				U.S. PATENT DOCUMEN	rs	
Examiner Initials	Cite No.1	U.S. Patent Document		Name of Patentee or Applicant of Cited	Date of Publication of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ³ (if known)	Document	MM-DD-YYYY	
FD		5,531,862		Otsubo et al.	07/02/1996	
1		5,575,883		Nishikawa	11/19/1996	
		5,902,993		Okushiba et al.	05/11/1999	
		6,006,763		Mori et al.	12/28/1999	
V		4,086,020		Tanabe et al.	04/25/1978	
	1					
		<u> </u>				
		İ				
	1					

Passages or Relevant igures Appear T
gares Appear
e of the T ²

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, Washington, DC 20231.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

¹ Unique citation designation number. 2 Applicant is to place a check mark here if English language Translation is attached.

PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Substitut	te for form 1449A/PTO			Complete if Known			
EMARYLEO	RMATION I	nisc	LOSUDE	Application Number	10/712,062		
				Filing Date	November 14, 2003		
STATEMENT BY APPLICANT				First Named Inventor	Shunpei YAMAZAKI et al.		
ı	(use as many sheets a	as necesso	(עמנ	Group Art Unit	2826		
				Examiner Name	F. Abraham		
Sheet	ı	of	1	Attorney Docket Number	0756-7218		
	1	1			ŀ		

				U.S. PATENT DOCUMEN	TS	
Examiner Initials	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited	Date of Publication of Cited Document	Pages, Columns, Lines, Where Relevan Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)	Document	MM-DD-YYYY	
1,8		5,970,327		Makita et al	10/19/1999	
		6,177,302		Yamazaki et al.	01/23/2001	
		6,465,287		Yamazaki et al.	10/15/2002	
		6,482,686		Takemura	11/19/2002	7
		6,495,404		Teramoto et al.	12/17/2002	
V	<u> </u>	6,528,358		Yamazaki et al.	03/04/2003	
		<u> </u>				
	<u> </u>	<u> </u>				
	<u> </u>					
	<u> </u>	<u></u>				
		<u> </u>				
	L					
			1		1	

Initials No.			Name of Patentee or	Decument	Relevant Passages or Relevant		
	Office)	Kind Code ³ Number ⁴ (if known)	Applicant of Cited Document	Document MM-DD-YYYY	Figures Appear	T*	
		OTHER PRI	OR ART - NON PATENT LITE	RATURE DOCUMENTS	<u> </u>		
Examiner Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.)., date, page(s), volume-issue number(s), publisher, city and/or country where published.						

Examiner	A	Land 1	Date	2/0/	7
Signature	cela) resour	Conside		

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, Washington, DC 20231.

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ³ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

¹ Unique citation designation number. ² Applicant is to place a check mark here if English language Translation is attached.

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number. Complete if Known Substitute for form 1449A/PTO Based on 10/214,691 Application Number INFORMATION DISCLOSURE August 9, 2002 Filing Date STATEMENT BY APPLICANT Shunpei YAMAZAKI, et al. First Named Inventor (use as many sheets as necessary) 2826 Group Art Unit Fetsum Abraham **Examiner Name** Sheet 12 Attorney Docket Number 0756-7218

			U.S. PATENT DOCUMENT	rs		
Examiner Initials	Cite No.	U.S. Patent Document Number Kind Code ² (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
Pp		5,686,328	Zhang et al.	11/11/97		
T		5,763,899	Yamazaki et al.	06/09/98		
		5,782,665	Weisfield et al.	07/21/98		
	-	5,922,125	Zhang	07/13/99		
		6,083,801	Ohtani	07/04/00		
		5,744,822	Takayama et al.	04/28/98		
		5,744,824	Kousai et al.	04/28/98)	
		5,766,977	Yamazaki	06/16/98		
		5,773,846	Zhang et al.	06/30/98	/	
		5,773,847	Hayakawa	06/30/98	(
		5,773,327	Yamazaki et al.	06/30/98		
		5,795,795	Kousai et al.	08/18/98		
		5,808,321	Mitanaga et al.	09/15/98)	
		3,890,632	Ham et al.	06/17/75		
		4,330,363	Biefesen et al.	05/18/82		
	-	4,466,073	Boyan et al.	08/14/84		
		5,543,636	Yamazaki	08/06/96	/	
		6,140,165	Zhang et al.	10/31/00		
		6,147,667	Yamazaki et al.	11/14/00		
		6,180,439 B1	Yamazaki et al.	01/30/01		
		5,929,527	Yamazaki et al.	07/27/99		
		5,949,107	Zhang	09/07/99		
		6,031,249	Yamazaki et al.	02/29/00		
		6,121,683	Yamazaki et al.	09/19/00		
		6,207,969 BI	Yamazaki et al:	03/27/01		

		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the No. item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
		Japan J. Appl. Phys. 8 (1969) 1056, "Effect of Deposited Metals on the Crystallization Temperature of Amorphous Germanium Film," OKI et al.				
		Technology Information Association, "Thermo-Auto-Chrome Full Color Recording Technology," May 31, 1995	-			

Examiner Signature Character Considered 2/8/05

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

Please type a plus sign (+) inside this box → [+]

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitut	e for form 1449A/PTO		· · · · · · · · · · · · · · · · · · ·	Complete if Known		
INFO	RMATION I	DISC	LOSURE	Application Number	Based on 10/214,691	
STATEMENT BY APPLICANT				Filing Date	August 9, 2002	
SIA				First Named Inventor	Shunpei YAMAZAKI, et al.	
	(use as many sheets t	u necesso	ייי)	Group Art Unit	2826	
				Examiner Name	Fetsum Abraham	
Sheet	2	of	12	Attorney Docket Number	0756-7218	

			U.S. PATENT DOCUMEN	ГS	
Examiner Initials	Cite No. ¹	U.S. Patent Document Number Kind Code ²	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	ļ	(if known)	<u> </u>		
FR		5,811,327	Funai et al.	09/22/98	
	ļ	5,818,076	Zhang et al.	10/06/98	
		5,821,138	Yamazaki et al.	10/13/98	
		5,824,574	Yamazaki et al.	10/20/98	
	<u> </u>	6,175,348	Zhang et al.	01/16/01	
		5,728,259	Suzawa et al.	03/17/98	
		6,278,132 B1	Yamazaki et al.	08/21/01	
		5,818,076	Zhang et al.	10/06/98	
		3,389,024	Schimmer	06/18/68	
		3,783,049	Sandera.	01/01/74	
i		4,059,461	Fan et al.	11/22/77	
		4,068,020	Reuschel	01/10/78	
		4,132,571	Cuomo et al.	01/02/79	
		4,174,217	Flatley	11/13/79	
		4,226,898	Ovshinsky et al.	10/07/80	
		4,231,809	Schmidt	11/04/80	
		4,271,422	Ipri	06/02/81	\
		4,277,884	Hsu	07/14/81	
		4,300,989	Chang	11/17/81	/
		4,309,224	Shibata	01/05/82	
		4,331,709	Risch et al.	05/25/82	/
		4,379,020	Glaeser et al.	04/05/83	/
,		4,409,724	Tasch, Jr., et al.	10/18/83	
		4,472,458	Sirinyan et al.	09/18/84	
		4,481,121	Barthel	11/06/84	
		4,534,820	Mori et al.	08/13/85	
		4,544,418	Gibbons	10/01/85	

			F	OREIGN PATENT DOC	UMENTS		
Cite No.	Foreign Patent Document		Name of Patentee or	Date of Publication of Cited	Pages, Columns, Lines, Where		
	Office ³	Number ⁴	Kind Code ³ (if known)	Applicant of Cited Document	MM-DD-YYYY	Figures Appear	T*
	JP	07-335900		Teramoto Satoshi	12/22/95		Abst.
	JP	64-081324	-		03/27/89		Abst.
		от	HER PRIOR	ART - NON PATENT LITE	RATURE DOCUMENTS		
Cite No.1		Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.)., date, page(s), volume-issue number(s), publisher, city and/or country where published.					
	ВМ	Technical	Disclosure	Bulletin, Vol. 11, No	o.7, A.R. Baker, Jr.		
	No.1	No.¹ Office¹ JP JP Cite No.¹	No.¹ Office³ Number⁴ JP 07-335900 JP 64-081324 OT Cite No.¹ Include no item (book	Cite No. Foreign Patent Document	Cite No. 1 Description Patent Document Name of Patentee or Applicant of Cited Document	No.¹ Name of Patentee or Applicant of Cited Document Name of Cited	Cite No. 1 Foreign Patent Document Number Name of Patentee or Office Number Kind Code (If Incom) Name of Patentee or Applicant of Cited Document MM-DD-YYYY Pages, Columns, Lines, Where Relevant Passages or Relevant Passages

				_
Examiner	My Alah	Date	2/0/01	
Signature	all Horan	Considered	2/0/03	

	e a plus sign (+) insid			U.S. Patent and Tradema	PTO/SB/08A (08-00) roved for use through 10/31/2002. OMB 0651-0031 ark Office: U.S. DEPARTMENT OF COMMERCE ion unless it contains a valid OMB control number.
Substitut	te for form 1449A/PTO			C	Complete if Known
INEC	INFORMATION DISCLOSURE		Application Number	Based on 10/214,691	
	STATEMENT BY APPLICANT			Filing Date	August 9, 2002
SIA	_			First Named Inventor	Shunpei YAMAZAKI, et al.
	(use as many sheets	as necess	ary)	Group Art Unit	2826
				Examiner Name	Fetsum Abraham
Sheet	3	of	12	Attorney Docket Number	0756-7218

			U.S. PATENT DOCUMEN	TS	
Examiner Initials	Cite No.1	U.S. Patent Document Number Kind Code ³ (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
B		4,546,376	Nakata et al.	10/08/85	
	†	4,597,160	Ipri	07/01/86	
		4,634,473	Swartz et al.	01/06/87	/
		4,735,824	Yamabe et al.	04/05/88	 /
		4,755,481	Faraone	07/05/88	
		4,911,781	Fox et al.	03/27/90	
		4,959,247	Moser et al.	09/25/90	
		4,959,700	Yamazaki	09/25/90	
		4,996,077	Mosiehi et al.	02/26/91	\
		4,996,523	Bell et al.	02/26/91	\
		5,043,224	Jaccodine et al.	08/27/91	, , , , , , , , , , , , , , , , , ,
		5,075,259	Moran	12/24/91	
	<u> </u>	5,089,441	Mosiehi	02/18/92	/
		5,112,764	Mitra et al.	05/12/92	
		5,145,808	Sameshima et al.	09/08/92	
		5,147,826	Liu et al.	09/15/92	/
		5,173,446	Asakawa et al.	12/22/92	/
		5,200,630	Nakamura et al.	04/06/93	/
		5,221,423	Sugino et al.	06/22/93	l - (
<u> </u>		5,225,355	Sugino et al.	07/06/93	
		5,244,836	Lim	09/14/93	
		5,254,480	Tran	10/19/93	
		5,262,350	Yamazaki et al.	11/16/93	
		5,262,654	Yamazaki	11/16/93	1
		5,275,851	Fonash et al.	01/04/94	
		5,278,093	Yonehara	01/11/94	
		5,289,030	Yamazaki et al.	02/22/94	/
		5,296,405	Yamazaki et al.	03/22/94	
1		5,298,075	Lagendijk et al.	03/29/94	
	1	5,308,998	Yamazaki et al.	05/03/94	
		5,313,075	Zhang et al.	05/17/94	
		5,352,291	Zhang et al.	10/04/94	\
		5,354,697	Oostra et al.	10/11/94	\
		5,358,907	Wong	10/25/94	\
		5,366,926	Mei et al.	11/22/94	
		<i>5</i> ,387,530	Doyle et al.	02/07/95	
1		5,424,230	Wakai	06/13/95	\

	<u> </u>				
Examiner	1	March	Date	9/0/05	
Signature /	ehr	gerale	Considered	2/8/05	

	e a plus sign (+) ins			U.S. Patent and Tradema	PTO/SB/08A (08-00) oved for use through 10/31/2002. OMB 0651-0031 ork Office: U.S. DEPARTMENT OF COMMERCE on unless it contains a valid OMB control number.	
Substitute for form 1449A/PTO				Complete if Known		
INEC	RMATION	DISC	LOSURE	Application Number	Based on 10/214,691	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Filing Date	August 9, 2002	
SIA				First Named Inventor	Shunpei YAMAZAKI, et al.	
	(use as many sheet	is as necess	ary)	Group Art Unit	2826	
				Examiner Name	Fetsum Abraham	
Sheet	4	of	12	Attorney Docket Number	0756-7218	

			U.S. PATENT DOCUMEN	TS	
Examiner Initials	Cite No.1	U.S. Patent Document Number Kind Cod	Name of Patentee or Applicant of Cited	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
0		(if known)			
pro	<u> </u>	5,470,763	Hamada	11/28/95	
		5,480,811	Chiang et al.	01/02/96	
		5,504,019	Miyasaka et al.	04/02/96	
		5,508,207	Horai et al.	04/16/96	
		5,531,182	Yonehara	07/02/96	
		5,580,815	Hsu et al.	12/03/96	
		5,621,244	Yamazaki et al.	04/15/97	T
		5,661,311	Takemura et al.	08/26/97	1
		5,684,317	Hwang	11/04/97	
		5,684,365	Tang et al.	11/04/97	
		5,693,541	Yamazaki et al.	12/02/97	
<u>`</u>		5,696,003	Makita et al.	12/09/97	
		5,717,224	Zhang	02/10/98	
		5,734,179	Chang et al.	03/31/98	
		5,773,327	Yamazaki et al.	06/30/98	
		5,786,796	Takayama et al.	07/28/98	\
		5,821,560	Arai et al.	10/13/98	
i		5,828,429	Takemura	10/27/98	
1		5,838,508	Sugawara	11/17/98	
		5,843,225	Takayama et al.	12/01/98	
		5,846,857	Ju	12/08/98	
		5,849,611	Yamazaki et al.	12/15/98	
	Ĭ.	5,882,960	Zhang et al.	03/16/99	
:		5,888,858	Yamazaki et al.	03/30/99	
		5,895,933	Zhang et al.	04/20/99	
		5,899,547	Yamazaki et al.	05/04/99	
		5,929,464	Yamazaki et al.	07/27/99	1
		5,933,205	Yamazaki et al.	08/03/99	
		5,940,732	Zhang	08/17/99	
		5,962,869	Yamazaki et al.	10/05/99	1
		5,963,278	Yamazaki et al.	10/05/99	
		5,985,740	Yamazaki et al.	11/16/99	
		5,990,491	Zhang	11/23/99	
		5,990,542	Yamazaki	11/23/99	
1		6,005,648	Zhang et al.	12/21/99	`\
V		6,011,277	Yamazaki	01/04/00	

Examiner Date 7/c/p/s	
Signature	
Considered / 0 /	

Examiner Signature

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute	for form 1449A/PTO		_	Complete if Known		
INFO	RMATION I	חופרי	LOSURE	Application Number	Based on 10/214,691	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Filing Date	August 9, 2002	
SIA				First Named Inventor	Shunpei YAMAZAKI, et al.	
	(use as many sheets	as necesso	² /y)	Group Art Unit	2826	
				Examiner Name	Fetsum Abraham	
Sheet	5	of	12	Attorney Docket Number	0756-7218	

			U.S. PATENT DOCUMEN	TS		
Examiner Initials*	Cite No.'	U.S. Patent Document	Name of Patentee or Applicant of Cited	Date of Publication of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
		Number Kind Code (if known)	Document	MM-DD-YYYY		
HA		6,013,929	Ohtani	01/11/00		
	T -	6,048,758	Yamazaki et al.	04/11/00		
	1.	6,063,654	Ohtani	05/16/00)	
		6,077,731	Yamazaki et al.	06/20/00		
		6,093,934	Yamazaki et al.	07/25/00		
1		6,100,562	Yamazaki et al.	08/08/00		
T		RE 28,385	Mayer	04/08/75		
		RE 28,386	Heiman et al.	04/08/75		

			FC	DREIGN PATENT DOC	UMENTS		
Examiner Initials	Cite No.	Office ²	Foreign Patent Document Kind Code ³ Number ⁴ (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	1⁴
		EP	0 178 447		10/09/84		English
		JP	01-187814		07/27/89		Full
		JP	01-187874		07/27/89		Abst.
		JP	01-187875		07/27/89		Abst.
1		JP	01-206632	·	08/18/89		Abst.
		JP	02-140915		05/30/90		Full
		JP	02-148687		06/07/90		Abst.
		JP	02-275641		11/09/90		Abst.
		JP	03-280418		12/11/91		Abst.
		JP	03-280420		12/11/91		Full
		JP	05-082442		04/02/93		Abst.
	1	JP	05-107561		04/30/93		Abst.
		JP	05-299348		11/12/93		Abst.
		JP	06-232059		08/19/94		Full
		JP	07-161634		06/23/95		Abst.
		JP	07-321339		12/08/95		Abst.
		JP	08-129358		05/21/96		Abst.
1		JP	08-129359		05/21/96		Abst.
•		JP	08-129360		05/21/96		Abst.
		JP	08-234683		09/13/96		Abst.
	i	JP	08-241047		09/17./96		Abst.
		JP	08-241048		09/17/96		Abst.
		JP	08-241057		09/17/96		Abst.
		JP	08-241997		09/17/96		Abst.
		JP	60-105216		06/10/85		Full
1		JP	61-063017		04/01/86		Full
T_{-}		JP	61-063107		04/01/86		Abst.
₹		JР	62-169356		07/25/87		Abst.

Date Considered

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO				Complete if Known		
INFO	RMATION I) ISC	OSURE	Application Number	Based on 10/214,691	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Filing Date	August 9, 2002	
				First Named Inventor	Shunpei YAMAZAKI, et al.	
	(use as many sheets	as necesso	(עיי	Group Art Unit	2826	
				Examiner Name	Fetsum Abraham	
Sheet	6	of	12	Attorney Docket Number	0756-7218	

		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS							
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.							
Ro		Caune et al., "Combined CW Laser and Furnace Annealing of Amorphous Si and Ge in Contact With Some Metals," January 1, 1989, pp. 597-604, Applied Surface Science, Vol. 36							
		Stoemnos et al., "Crystallization of Amorphous Silicon by Reconstructive Transformation Utilizing Gold," March 18, 1991, pp. 1196-1198, Appl. Phys. Lett. 58(11)							
		Kakkad et al., "Crystallized Si-Films By Low-Temperature Rapid Thermal Annealing of Amorphous Silicon," March 1, 1989, pp. 2069-2072, J. Appl. Phys. 65(5)							
		Oki et al., "Effect of Deposited Metals On The Crystallization Temperature of Amorphous Germanium Film," 1969, pp. 1056, Jpn. J. Appl. Phys. 8							
		Kuznetsov et al., "Enhanced Solid Phase Epitaxial Recrystallization of Amorphous Silicon Due to Nickel Silicide Precipitation Resulting From Ion Implantation and Annealing," 1993, pp. 990-993, Nucl. Instruments Methods Physics Research, 880/881							
1		Hayashi et al., "Fabrication of Low-Temperature Bottom Gate Poly-Si TFTs on Large Area Substrate by Linear-Beam Excimer Laser Crystallization and Ion Doping Method," January 1, 1995, pp. 829-832, IEEE IEDM							
		Takenaka et al., "High Mobility Poly-Si Thin Film Transistors Using Solid Phase Crystallized a-Si Films Deposited by Plasma Enhanced Chemical Vapor Deposition," December 1990, pp. L2380-L2383, Jpn. J. Appl. Phys. Vol 29, No. 12							
		Hatalis et al., "High Performance Thin-Film Transistors in Low Temperature Crystallized LPCVD Amorphous Silicon Films," August 1987, pp. 361-364, Elec. Dev. Letters Vol. EDL 8, No. 8							
		Zorabedian et al., "Lateral Seeding of Silicon-on-Insulator Using an Elliptical Laser Beam: A Comparison of Scanning Methods," 1984, pp. 81-86, Mat. Res. Soc. Symp. Proc. Vol. 33							
		Green et al., "Method to Purify Semiconductor Wafers," October 1973, pp. 1612-1613, IBM Tech. Discl. Bulletin, Vol. 16, No. 5							
1		Boyd, et al., "Oxidation of Silicon Surfaces by CO2 Lasers," July 15, 1982, pp. 162-164, Applied Phys. Letters, Vol. 41, No. 2	1=						
J		Wolf et al., "Silicon Processing for the VLSI Era Volume 1: Process Technology," 1986, pp. 215-216, Lattice Press							
Examiner	1 .	LA							
Signature	1 /	Elw Abraha Date Considered 2/8/05							

Please type a plus sign (+) inside this box → [+]

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute	for form 1449A/PTO			Complete if Known		
INFO	RMATION I	DISC	LOSURE	Application Number	Based on 10/214,691	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Filing Date	August 9, 2002	
SIAI				First Named Inventor	Shunpei YAMAZAKI, et al.	
	(use as many sheets t	as necesso	(עיי	Group Art Unit	2826	
				Examiner Name	Fetsum Abraham	
Sheet	7	of	12	Attorney Docket Number	0756-7218	

		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS	
Examiner nitials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.)., date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
fo		Lau et al., "Solid Phase Epitaxy in Silicide Forming System," 1977, pp. 313-322, Thin Solid Films, 47	
		Kawazu et al., "Low-Temperature Crystallization of Hydrogenated Amorphous Silicon Induced by Nickel Silicide Formation," December 1990, pp. 2698-2704, Inst. Of Appl. Phys. Vol. 29, No. 12	
		Wolf et al., "Silicon Processing for the VLSI Era Volume 1 – Process Technology," 1986, pp. 550-551, Lattice Press	
:	-	Bruines et al., "Between Explosive Crystallization and Amorphous Regrowth: Inhomogeneous Solidification Upon Pulsed Laser Annealing of Amorphous Silicon," March 1, 1987, pp. 507-509, Applied Physics Letter, Vol. 50	
		Kawazu et al., "Initial Stage of the Interfacial Reaction between Nickel and Hydrogenated Amorphous Silicon," April 1, 1990, pp. 729-738, Japanese Journal of Appl. Phys., Vol.29	
		Kakkad et al., "Low Temperature Selective Crystallization of Amorphous Silicon," 1989, pp. 66-68, Journal of Non-Crystalline Solids, 115	
		Suresh et al., "Electroless Plated Nickel Contacts to Hydrogenated Amorphous Silicon," January 1, 1994, pp. 78-81, Thin Solids Films, Vol. 252	
		Sakaguchi et al., "Current Progress in Epitaxial Layer Transfer," March 1, 1997, pp. 378-387, IEICE Trans. Electron, Vol. E80 C/No. 3	
		Kouvatsos et al., "Fluorine-Enhanced Oxidation of Polycrystalline Silicon and Application to Thin-Film Transistor Fabrication," August 24, 1992, pp. 937-939, Appl. Phys. Letter, Vol. 61, No. 8	
ĺ		Sze, "VLSI Technology," January 1, 1988, pp. 397-400, McGraw-Hill Publishing Company, Second Edition	
1		Ghandhi, "VLSI Fabrication Principles," January 1, 1983, pp. 419-429, Wiley and Sons	
i		Kuper et al., "Effects of Fluorine Implantation on the Kinetics of Dry Oxidation of Silicon," August 1, 1986, pp. 985-990, J. Applied Physics	
		Wolf et al., "Silicon Processing for the VLSI Era Volume 1: Process Technology," 1986, pp. 198-207, Lattice Press	

						<u> </u>
Examiner	14	-00	Date	0/0	100	
Signature	Celm	46val-	Considered	ر ۵ / ک	05	

	Please type a plus sign (+) inside this box → [+] Approved for use through 10/31/2002. OMB 0651-0031 U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.									
Substitute for form 1449A/PTO INFORMATION DISCLOSURE				Complete if Known						
			LOSURE	Application Number	Based on 10/214,691					
_	EMENT BY			Filing Date	August 9, 2002					
SIAI				First Named Inventor	Shunpei YAMAZAKI, et al.					
	(use as many sheets o	is necesso	(ציו	Group Art Unit	2826					
				Examiner Name	Fetsum Abraham					
Sheet	8	of	12	Attorney Docket Number	0756-7218					

Examiner Cite Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the									
Initials	No.1	item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	1*						
The		Thompson et al., "Silicide Formation in Pd-a-Si:H Schottky Barriers," August 1981, pp. 274-276, Appl. Phys. Lett., Vol. 39, No. 3							
		Nemanich et al., "Initial Phase Formation at the Interface of Ni, Pd, or Pt and Si," 1984, pp. unknown, Mat. Res. Soc. Symp. Proc., Vol. 25							
		Nemanich et al., "Structure and Growth of the Interface of Pd on a-SiH," June 15, 1981, pp. 6828-6831, The American Physical Society Physics Review, Vol. 22, No. 12							
		Hemple et al., "Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Film," 1993, pp. 921-924, Solid State Communications, Vol. 85, No. 11							
		Kuo, "Thin Film Transistor Technologies," Vol. 94-35, pp. 116-122, The Electrochemical Society Proceedings							
		Author Unknown, "Thermo Auto-Chrome Full Color Recording Technology," May 31, 1995, pp. Unknown, Technology Information Association							
		Wolf et al., "Thermal Oxidation of Single Crystal Silicon," 1986, pp. 207-211, Silicon Processing for the VLSI Era							
i		Erokhin et al., "Spatially Confined Nickel Disilicide Formation at 400C on Ion Implantation Preamorphized Silicon," Dec. 6, 1993, pp. 3173-3175, Appl. Phys. Lett. 63 (23)							
1		Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals," 1986, pp. 635-640, Akademikian Lavrentev Prospekt 13, 630090 Novosibirsk 90, USSR							
		Batstone et al., "Microscopic Processes in Crystallization," January 1, 1994, pp. 257-268, Solid State Phenomena, Vol. 37-38							
		Cammarata et al., "Silicide Precipitation and Silicon Crystallization in Nickel Implanted Amorphous Silicon Thin Films," Oct 10, 1990, pp. 2133-2138, J. Mater. Res. Vol. 5, No. 10							
V		Hayzelden et al., "Silicide Formation and Silicide Mediated Crystallization of Nickel- Implanted Amorphous Silicon Thin Films," May 15, 1993, pp. 8279-8289, J. Appl. Phys. 73(12)							

			·				
Examiner		θ	1001	Date	2/	<u>v /</u>	21
Signature	///	\sim χ	man	Considered		0 //	00

Please type a plus sign (+) inside this box → {+}

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute	Substitute for form 1449A/PTO			Complete if Known		
INFO	RMATION I	DISC	LOSURE	Application Number	Based on 10/214,691	
	INFORMATION DISCLOSURE STATEMENT BY APPLICANT			Filing Date	August 9, 2002	
SIAI				First Named Inventor	Shunpei YAMAZAKI, et al.	
}	(use as many sheets o	as necesso	(עינו	Group Art Unit	2826	
				Examiner Name	Fetsum Abraham	
Sheet	9	of	12	Attorney Docket Number	0756-7218	

				U.S. PATENT DOCUMEN	TS	
Examiner Initials	Cite No.1	U.S. Patent Document		Name of Patentee or Applicant of Cited	Date of Publication of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ¹ (if known)	Document	MM-DD-YYYY	
14		5,705,829		Miyanaga et al.	01/06/98	/;
		5,712,191		Nakajima et al.	01/27/98	
		5,756,364		Tanaka et al.	05/26/98	
		5,619,044		Makita et al.	04/08/97	
		5,530,266		Yonehara et al.	06/25/96	
		5,550,070		Funai et al.	08/27/96	
		5,693,959		Inoue et al.	12/02/97	

		OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS	
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.)., date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ₃
		Kuznetsov et al., "Silicide Precipitate Formation and Solid Phase Re-Growth of Ni- Implanted Amorphous Silicon," April 5-8, 1993, pp. 191-194, Inst. Phys. Conf. Ser. No. 134.4: Proceedings of Royal Microscipical Society Conf.	
		Liu et al., "Polycrystalline Silicon Thin Film Transistors on Corning 7059 Glass Substrates Using Short Time, Low-Temperature Processing," May 17, 1993, pp. 2554-2556, Appl. Phys. Lett 62(20)	
		Liu et al., "Selective Area Crystallization of Amorphous Silicon Films by Low- Temperature Rapid Thermal Annealing," August 14, 1989, pp. 660-662, Appl. Phys. Lett 55(7)	
V		Spaepen et al., Metal-Enhanced Growth of Silicon, 1992, pp. 483-499, Crucial Issues in Semiconductor Materials & Processing Technologies	

Examiner Signature Date oí Considered

Approved for use through 10/31/2002. OMB 0651-0031
U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Complete if Known Substitute for form 1449A/PTO Based on 10/214,691 Application Number INFORMATION DISCLOSURE August 9, 2002 Filing Date STATEMENT BY APPLICANT Shunpei YAMAZAKI, et al. First Named Inventor (use as many sheets as necessary) 2826 Group Art Unit Fetsum Abraham Examiner Name Sheet Attorney Docket Number 0756-7218

U.S. PATENT DOCUMENTS								
Examiner Initials	Cite No.'	U.S. Patent Document	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear			
		Number Kind Code ³ ((f known)						
18		5,403,772	Zhang et al.	04/04/95				
7		5,426,064	Zhang et al.	06/20/95				
		5,481,121	Zhang et al.	01/02/96				
		5,488,000	Zhang et al.	01/30/96				
		5,492,843	Adachi et al.	02/20/96				
		5,501,989	Takayama et al.	03/26/96				
		5,508,533	Takemura	04/16/96				
		5,529,937	Zhang et al.	06/25/96				
		5,534,716	Takemura	07/09/96				
		5,543,352	Ohtani et al.	08/06/96				
		5,563,426	Zhang et al.	10/08/96				
i		5,569,610	Zhang et al.	10/29/96				
		5,569,936	Zhang et al.	10/29/96				
		5,580,792	Zhang et al.	12/03/96				
		5,585,291	Ohtani et al.	12/17/96				
		5,589,694	Takayama et al.	12/31/96				
		5,595,923	Zhang et al.	01/21/97				
		5,595,944	Zhang et al.	01/21/97	/			
		5,604,360	Zhang et al.	02/18/97	1			
		5,605,846	Ohtani et al.	02/25/97				
		5,606,179	Yamazaki et al.	02/25/97				
		5,608,232	Yamazaki et al.	03/04/97				
		5,612,250	Ohtani et al.	03/18/97	`\			
		5,614,426	Funada et al.	03/25/97	1			
		5,614,733	Zhang et al.	03/25/97				
		5,616,506	Takemura	04/01/97				
=		5,620,910	Teramoto	04/15/97	 			
· · · · · · · · · · · · · · · · · · ·		5,621,224	Yamazaki et al.	04/15/97				
	· ·	5,624,851	Takayama et al.	04/29/97				
		5,637,515	Takemura	06/10/97				
	<u> </u>	5,639,698	Yamazaki et al.	06/17/97	1-/			
		5,643,826	Ohtani et al.	07/01/97	/			
	 	5,646,424	Zhang et al.	07/08/97				
	 	5,654,203	Ohtani et al.	08/05/97				
-		5,656,825	Kusumoto et al.	08/12/97	<u>† </u>			
		5,663,077	Adachi et al.	09/02/97				
		5,677,549	Takayama et al.	10/14/97				
	†	5,696,386	Yamazaki	12/09/97				
/		5,696,388	Funada et al.	12/09/97	<u> </u>			
/	 	5,700,333	Yamazaki et al.	12/23/97				

Examiner Signature	Feth	Hoah	Date Considered	2/	8/03	
	1.					

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control numb

Substitut	Substitute for form 1449A/PTO			Complete if Known		
INFORMATION DISCLOSURE				Application Number	Based on 10/214,691	
STATEMENT BY APPLICANT				Filing Date	August 9, 2002	
SIA				First Named Inventor	Shunpei YAMAZAKI, et al.	
	(use as many sheets	as necesso	(עייי)	Group Art Unit	2826	
		_		Examiner Name	Fetsum Abraham	
Sheet	11	of	12	Attorney Docket Number 0756-7218		

Examiner Initials	Cite No.'	U.S. Patent Document	Name of Patentee or Applicant of Cited	Date of Publication of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
	No.	Number Kind Cod	le ² Document	MM-DD-YYYY			
PR		5,932,893	Miyanaga et al.	08/03/99			
1		4,759,610	Yanagisawa	07/26/88	,		
		5,535,471	Guldi	07/16/96			
		5,661,056	Takeuchi	08/26/97			
		4,140,548	Zimmer	02/20/79			
		5,210,050	Yamazaki et al.	05/11/93			
		5,298,075	Lagendijk et al.	03/29/94			
		5,306,651	Masumo et al.	04/26/94	I (
		5,313,076	Yamazaki et al.	05/17/94			
	5,365,080		Yamazaki et al.	11/15/94			
		5,372,860	Fehlner et al.	12/13/94)		
		5,591,988	Arai et al.	01/07/97			
		5,893,730	Yamazaki et al.	04/13/99			
1,		5,913,111	Kataoka et al.	06/15/99			
1/		5,953,597	Kusumoto et al.	09/14/99			
V.		6,011,275	Ohtani et al.	01/04/00			
7		6,133,073	Yamazaki et al.	10/17/00			
		OTHER	PRIOR ART - NON PATENT LITERAT	TURE DOCUMENTS			
Examiner Initials	Cite No. ¹		f the author (in CAPITAL LETTERS), title azine, journal, serial, symposium, catalog, e publisher, city and/or country w	tc.)., date, page(s), volume-issi			
PA		Wolf, Silicon Proce	ssing for the VLSI Era, Volume	2, Chapter 4, page 2	74 (1990).		
		/ (· · · · · · · · · · · · · · · · · · ·				
1							

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, Washington, DC 20231.

¹ Unique citation designation number. 2 See attached Kinds of U.S. Patent Documents. 2 Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

¹ Unique citation designation number. 2 Applicant is to place a check mark here if English language Translation is attached.

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Substitut	e for form 1449A/PTO			Complete if Known			
INFO	RMATION 1	nisc	LOSURE	Application Number	Based on 10/214,691		
	TEMENT BY			Filing Date	August 9, 2002		
SIA.	•			First Named Inventor	Shunpei YAMAZAKI, et al.		
	(use as many sheets	as necess	ary)	Group Art Unit	2826		
				Examiner Name	Fetsum Abraham		
Sheet	12	of	12	Attorney Docket Number	0756-7218		

				U.S. PATENT DOCUMENT	ΓS			
Examiner faitus'	Cite No.'	U.S. Patent Document		Name of Patentee or Applicant of Cited	Date of Publication of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
		Number	Kind Code ² (if known)	Document	MIM-DD-YYYY			
70		6,225,152	B1	Yamazaki et al.	05/01/01			
		6,288,412 B1 6,323,072 B1 6,331,718 B1		Hamada et al.	09/11/01			
				Yamazaki et al.	11/27/01			
1				Yamazaki et al.	12/18/01			
				·				
<u></u>	<u> </u>							
						<u> </u>		

					FOREIGN PATENT DOC	UMENTS		,
Examiner Initials	Cite No. ¹		Foreign Patent D		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
		Office	Number ⁴	Kind Code ³ (if known)				T ⁴
10		JP	06-31478	35		11/08/94		Ab
		JP	06-31478	37		11/08/94		Ab
<u> </u>								
	<u> </u>							
			0	THER PRIO	R ART – NON PATENT LITI	ERATURE DOCUMENTS		
Examiner Initials	Cite No. ¹				thor (in CAPITAL LETTERS), journal, serial, symposium, cata publisher, city and/or cour	log, etc.)., date, page(s), volum		T
		1						
		<u> </u>						
		}						
		<u>{ </u>						į
	T 5/2	0	 //				//	
Examiner Signature	1 %	The s	Solal			Pate 2	10/05	

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Considered

Signature

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, Washington, DC 20231.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

¹ Unique citation designation number. ² Applicant is to place a check mark here if English language Translation is attached.

Under the	Paperwo	ork Redu	ction Act of 1995, no	persons (are re	U.S. Patent and I	Frad	emark Office: 1	J.S. ĎEF	PARTMENT OF CON ains a valid OMB control	MERCE		
Substitut	te for for	n 1449A	/PTO			Complete if Known							
INIEO	OR# A	TION	I DISCLOS	Tibe		Application Number		10/71	2,062				
INFO			DISCHOS	# K-		Filing Date			November 14, 2003				
			ay a ppelic	ANI	رم ا	First Named Inventor				pei YAMAZAKI e	t al.		
	(use as	many sh	eets as necessary)	c 2004	48	Group Art Unit			2826				
			HOV 1	ם שעה	بخ	Examiner Name			F. Ab	raham			
Sheet	1		2		8	Attorney Docket Numb	er		0756-	7218			
	C Dungley												
	U.S. PATENT DOCUMENTS												
Exeminer Initials	Cite No.'	Nun					Date of Publicator Document MM-DD-YY	nt Relevant Passages or F		Relevant			
FA	1	6,1	162,704	1	Yan	nazaki et al.		12/19/2000					
T	1		94,441			nazaki		09/25/2001					
	1		161,943	-		nazaki et al.		10/08/2002					
	T		20,711			nazaki		09/16/2003					
			194,254	7	Γak	emura		02/27/2001					
										· · · · · · · · · · · · · · · · · · ·			
					OR	EIGN PATENT DOCL							
Examiner Initials	Cite No. ¹			Code ³ nown)		Name of Patentee or Applicant of Cited Document		Date of Publication of Cited Document MM-DD-YYYY		Pages, Columns, Lines, There Relevant Passages Relevant Figures Appear	T [©]		
		JР	07-066425		1		03	3/10/1995		<u> </u>	Abst. &		
											U.S. Equiv.		
		JP	08-045839				02	2/16/1996			Abst. & U.S. Equiv.		
		JP	08-045840				02	2/16/1996			Abst. & U.S. Equiv.		
		JP	08-097169				04	1/12/1996			Abst. & U.S.		
		KR	96-005879		+		02	2/23/1996			Equiv. U.S. Equiv.		
		JP	07-045519				02	2/14/1995			Abst. & U.S.		
		JP	07-231100		\dagger		08	3/29/1995			Equiv. Abst. & U.S. Equiv.		
/		JP	07-094757				04	4/07/1995		1	Abst. & U.S. Equiv.		
4		JP	07-335906				12	2/22/1995			Abst. & U.S. Equiv.		
	•		OTHE	R PRIOR	AR	T - NON PATENT LITE	RATI	URE DOCUMENT	s	· · · · · · · · · · · · · · · · · · ·			
Examiner Initials	Cite No.1				nal, s	n CAPITAL LETTERS), t serial, symposium, catalo ublisher, city and/or count	g, e	tc.)., date, page(s)			T ²		

Examiner Signature Policy (Signature Considered Whether or not citation is in conformance with MPEP 609. Draw line through citation if

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Signature

Substitute for form 1449A/PTO						Complete if Known						
INFO	RΜΔ	TION	DISCLAS	I PR	>	Application Number			10/71	2,062		
OTAT	FERRE	ENT D	APPLIC	A NIT	•	Filing Date			November 14, 2003			
				ANI	1	First Named Invent	or		Shunpei YAMAZAKI et al.			
	(use as	many sheel	s as ecessary)	1 5 2	1004	Goup Art Unit			2826			
			\~	•		kaminer Name			F. Abı	raham		
Sheet	2		01		- 4	Attorney Docket Nun	ber		0756-	7218		
U.S. PATENT DOCUMENTS												
Examiner Initials	Cite U.S. Patent Document					me of Patentee or Applicant of Cited Document MM-DD-YY			ent Relevant Passages or		Relevant	
2.			(if kno	vn)								
FA	_		/0025659			nazaki et al.		02/28/2002				
	 		/0048891			nazaki et al.		04/25/2002				
		6,42	3,586		Yan	nazaki et al.		07/23/2002				
1												
								<u> </u>		<u> </u>		
FOREIGN PATENT DOCUMENTS												
Exeminer Initials	Cite No.1 Foreign Patent Document				Name of Patentee or Applicant of Cited		ete of Publication of C Document MM-DD-YYYY	w	Pages, Columns, Lines, here Relevant Passages Relevant Figures Appear	T ⁴		
	Office ³ Number ⁴ (if known)					Document .						
i		JP (7-192998				0	7/28/1995			Abst.	
V		JP (05-299339				1	1/12/1993			Abst. & U.S. Equiv.	
					┸						ļ	
	<u> </u>	l l.			\perp				_			
				_	\perp		_					
	<u> </u>				┸							
					┸							
					4-		_	•				
	ļ				4			<u>-</u>				
											L	
			OTHE	R PRIO	RAR	T - NON PATENT LIT	ERAT	URE DOCUMENT	rs			
Examiner Initials	Cite No.1	ite			rnal,	n CAPITAL LETTERS) serial, symposium, catu ublisher, city and/or cou	alog, e	tc.)., date, page(s			T²	
Examiner	┰┰	LA	100		-		Date	<u> </u>	~ /	, 1, 1	<u></u>	

Considered

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.